

1N5400 - 1N5408

3.0A SILICON RECTIFIER

Features

- **Diffused Junction**
- Low Forward Voltage Drop
- **High Current Capability**
- High Reliability

High Surge Current Capability D

DO-201AD Dim Min Max Α 25.4 9.50 В 8.50 С 1.20 1.30 D 5.0 5.60 All Dimensions in mm

Mechanical Data

Case: Molded Plastic

Terminals: Plated Leads Solderable per MIL-STD-202, Method 208

Polarity: Cathode Band Weight: 1.2 grams (approx.) Mounting Position: Any Marking: Type Number

Epoxy: UL 94V-O rate flame retardant

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	1N 5400	1N 5401	1N 5402	1N 5404	1N 5406	1N 5407	1N 5408	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @T _A = 75°C	lo	3.0							Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	200							Α
Forward Voltage @I _F = 3.0A	VFM	1.0						V	
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	lкм	5.0 100							μΑ
Typical Junction Capacitance (Note 2)	Cj	50							pF
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{ heta}$ JA	18							K/W
Operating Temperature Range	Tj	-65 to +125							°C
Storage Temperature Range	Тѕтс	-65 to +150							°C

*Glass passivated forms are available upon request

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

